

REPLACEMENT CLAIMS

Cancel claim 11.

10. (Amended) A method of forming a contact comprising:

Sub B2 >

A2

providing a semiconductor stack including an active layer formed on a first insulator layer, wherein the first insulator layer is formed on a semiconductor substrate;

forming a gate dielectric over the active layer;

forming a gate electrode over the gate dielectric;

forming source and drain regions in the active layer and adjacent the gate electrode as to form a channel region underneath the gate electrode;

removing a portion of the active layer;

forming a second insulator layer adjacent the active layer and on the first insulator layer;

forming a doped region within the substrate by implanting through the first insulator layer;

forming a first opening in the second insulator layer and the first insulator layer; and

forming a conductive material within the first opening.

12. (Amended) The method of claim 10, wherein forming a doped region within the substrate further comprises implanting the first species through the second insulator layer and the active layer.

17. (Amended) A method of forming a contact comprising:

Sub B3 >

A3

providing a semiconductor stack including an active layer formed on a first insulator layer, wherein the first insulator layer is formed on a semiconductor substrate;

removing a portion of the active layer;

forming a second insulator layer adjacent the active layer and on the first insulator layer;

forming an opening in the second insulator layer and the first insulator layer;

forming a conductive material within the opening; and

forming a doped region within the substrate under the area of the opening by implanting through the first insulator layer.